

<IGBT Modules>

CM900DUC-24S

HIGH POWER SWITCHING USE
INSULATED TYPE



dual switch (Half-Bridge)

Collector current I_C **9 0 0 A**
 Collector-emitter voltage V_{CES} **1 2 0 0 V**
 Maximum junction temperature T_{jmax} **1 7 5 °C**

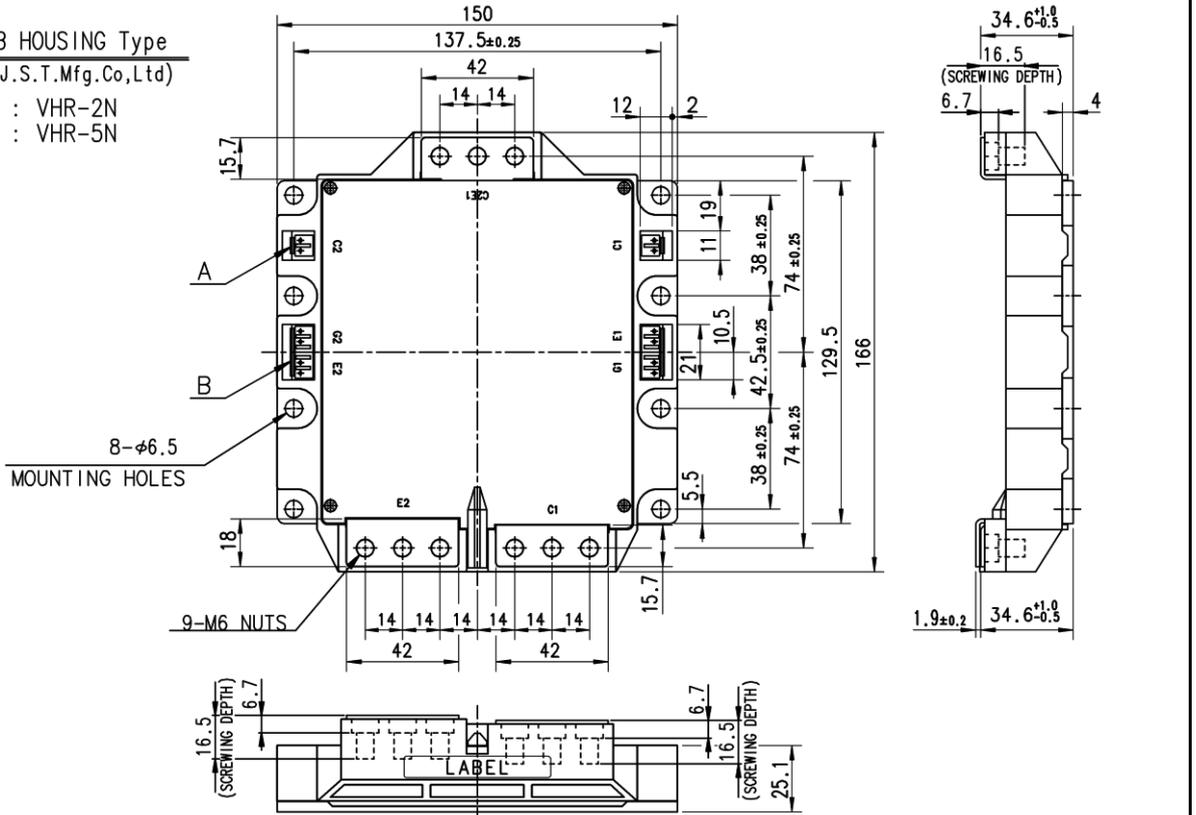
- Flat base Type
- Copper base plate (non-plating)
- RoHS Directive compliant
- Recognized under UL1557, File E323585

APPLICATION

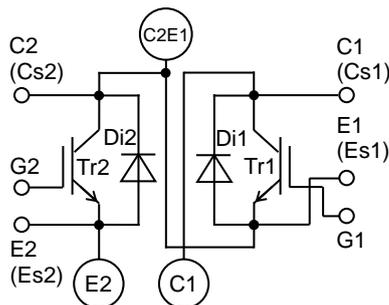
Wind power, Photovoltaic (Solar) power, AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

A,B HOUSING Type
 (J.S.T.Mfg.Co,Ltd)
 A : VHR-2N
 B : VHR-5N



INTERNAL CONNECTION



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

CM900DUC-24S

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=125\text{ }^\circ\text{C}$ (Note2, 4)	900	A
I_{CRM}		Pulse, Repetitive (Note3)	1800	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note2, 4)	6520	W
I_E (Note1)	Emitter current	DC (Note2)	900	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	1800	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T_{jmax}	Maximum junction temperature	Instantaneous event (overload)	175	$^\circ\text{C}$
T_{Cmax}	Maximum case temperature	(Note4)	125	$^\circ\text{C}$
T_{jop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	3.0	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=90\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
V_{CESat}	Collector-emitter saturation voltage	$I_C=900\text{ A}$ (Note5), $V_{GE}=15\text{ V}$, Terminal=chip	$T_j=25\text{ }^\circ\text{C}$	-	1.55	1.90	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.75	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.80	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	90	nF	
C_{oes}	Output capacitance		-	-	18		
C_{res}	Reverse transfer capacitance		-	-	1.5		
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=900\text{ A}$, $V_{GE}=15\text{ V}$	-	2300	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=900\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load	-	-	900	ns	
t_r	Rise time		-	-	250		
$t_{d(off)}$	Turn-off delay time		-	-	950		
t_f	Fall time		-	-	350		
V_{EC} (Note.1)	Emitter-collector voltage	$I_E=900\text{ A}$ (Note5), G-E short-circuited, Terminal=chip	$T_j=25\text{ }^\circ\text{C}$	-	1.65	2.10	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.65	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.65	-	
t_{rr} (Note1)	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_E=900\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	450	ns	
Q_{rr} (Note1)	Reverse recovery charge	$R_G=0\text{ }\Omega$, Inductive load	-	50	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C/I_E=900\text{ A}$,	-	68.9	-	mJ	
E_{off}	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$,	-	183	-		
E_{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	73.3	-	mJ	
$R_{CC'+EE'}$	Internal lead resistance	Main terminal-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4)	-	0.286	-	m Ω	
r_g	Internal gate resistance	Per switch	-	2.2	-	Ω	

CM900DUC-24S

HIGH POWER SWITCHING USE

INSULATED TYPE

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per IGBT (Note4)	-	-	23	K/kW
$R_{th(j-c)D}$		Junction to case, per DIODE (Note4)	-	-	39	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1/2 module, Thermal grease applied (Note4, 6)	-	12	-	K/kW

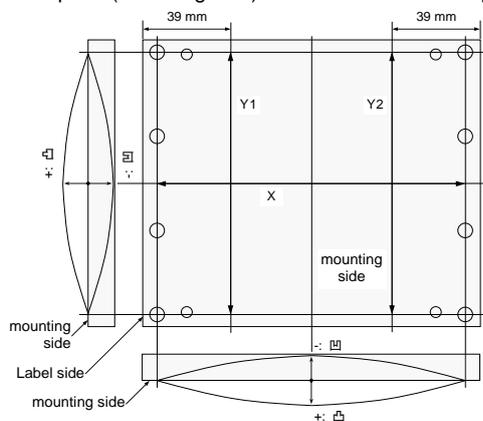
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M_s		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
d_s	Creepage distance	Terminal to terminal	24	-	-	mm
		Terminal to base plate	33	-	-	
d_a	Clearance	Terminal to terminal	14	-	-	mm
		Terminal to base plate	33	-	-	
m	mass	-	-	1450	-	g
e_c	Flatness of base plate	On the centerline X, Y1, Y2 (Note7)	-50	-	+100	μ m

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (DIODE).

2. Junction temperature (T_j) should not increase beyond T_{jmax} rating.
3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
4. Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
5. Pulse width and repetition rate should be such as to cause negligible temperature rise.
6. Typical value is measured by using thermally conductive grease of $\lambda=0.9$ W/(m·K).
7. Base plate (mounting side) flatness measurement points (X, Y1 and Y2) are as follows of the following figure.



8. The company name and product names herein are the trademarks and registered trademarks of the respective companies.

CM900DUC-24S

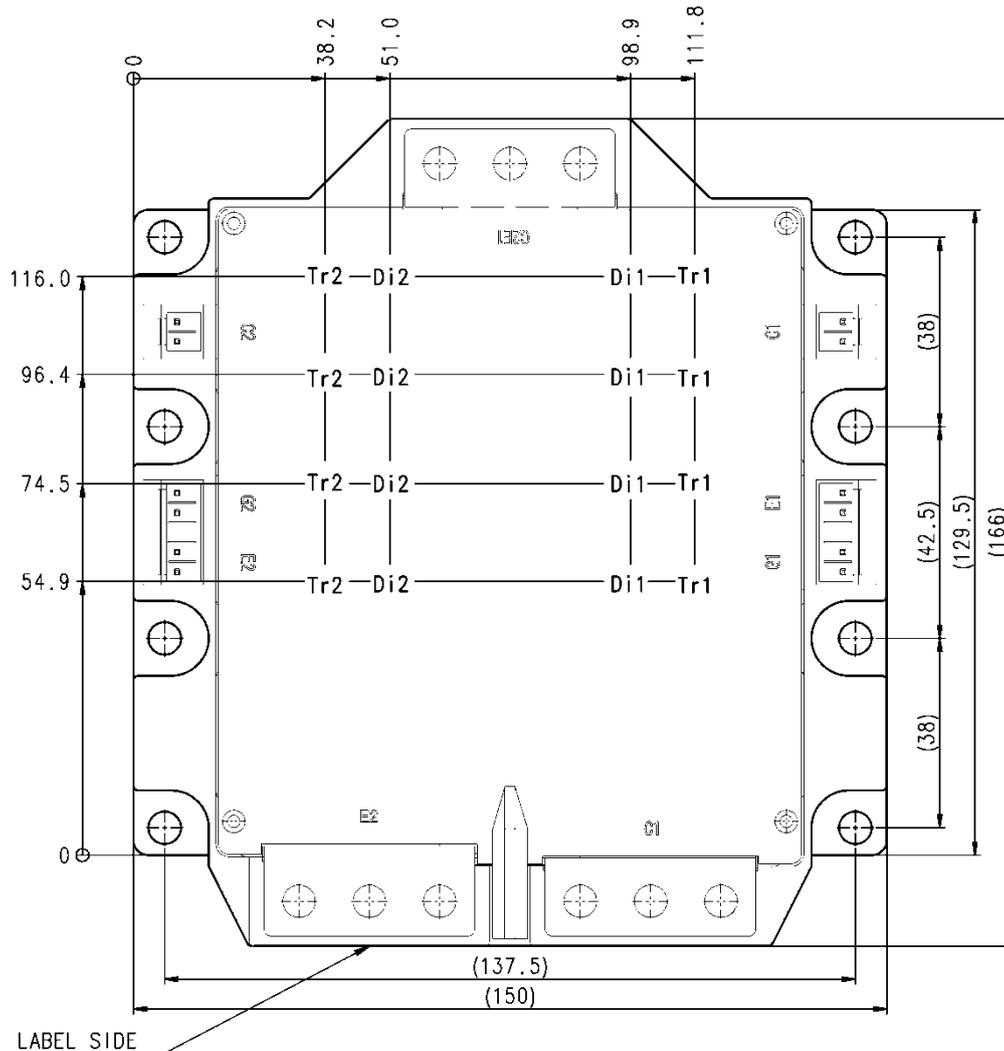
HIGH POWER SWITCHING USE
INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	850	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0	-	3.6	Ω

CHIP LOCATION (Top view)

Dimension in mm, tolerance: ± 1 mm

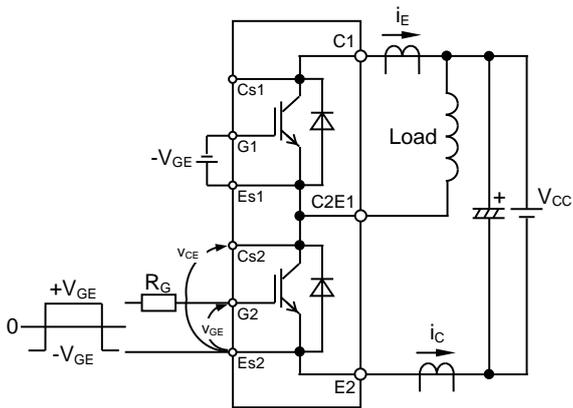


Tr1/Tr2: IGBT, Di1/Di2: DIODE

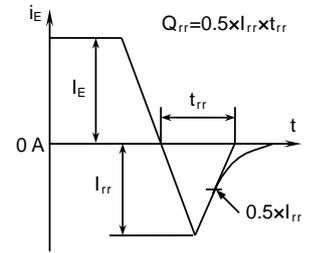
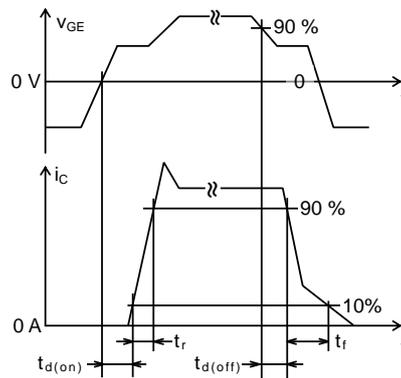
CM900DUC-24S

HIGH POWER SWITCHING USE
INSULATED TYPE

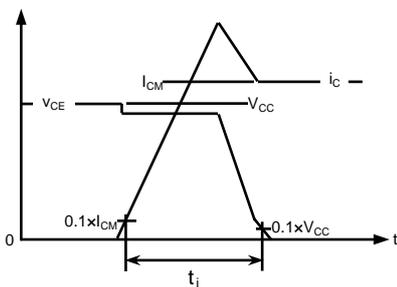
TEST CIRCUIT AND WAVEFORMS



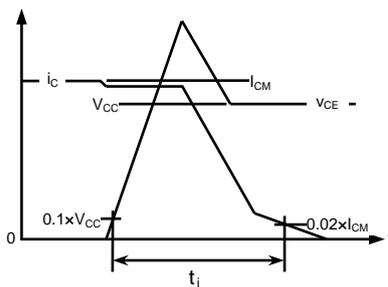
Switching characteristics test circuit and waveforms



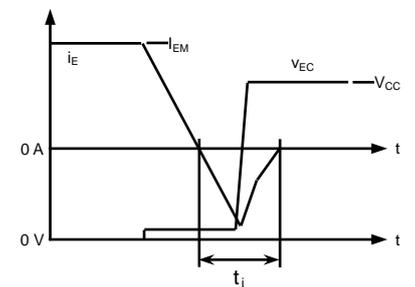
t_{rr} , Q_{rr} test waveform



IGBT Turn-on switching energy



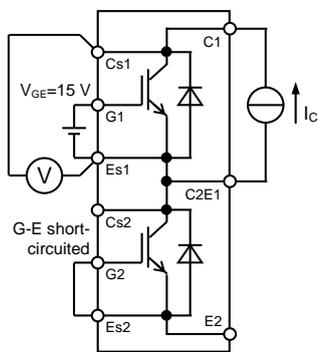
IGBT Turn-off switching energy



DIODE Reverse recovery energy

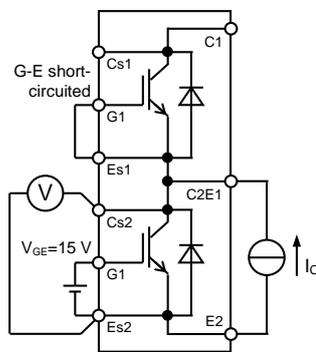
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

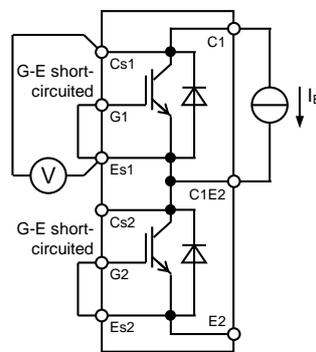


Tr1

V_{CEsat} test circuit

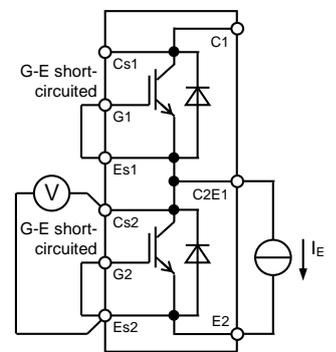


Tr2



Di1

V_{EC} test circuit



Di2

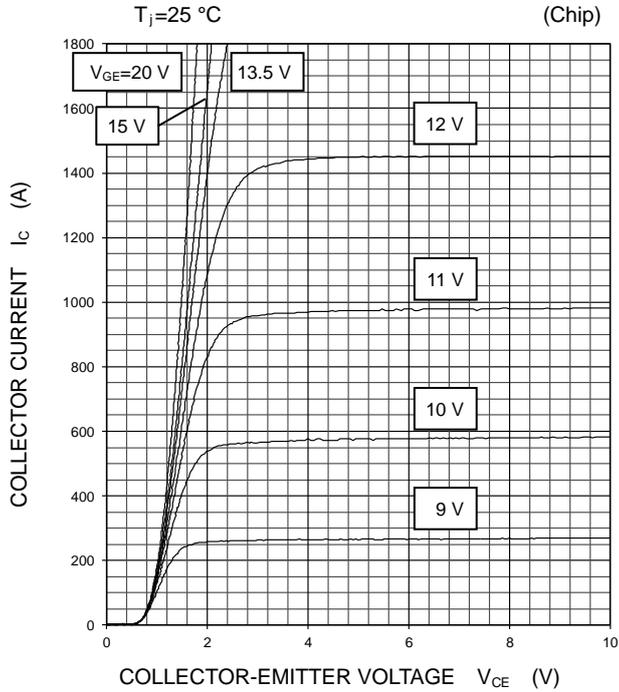
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HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

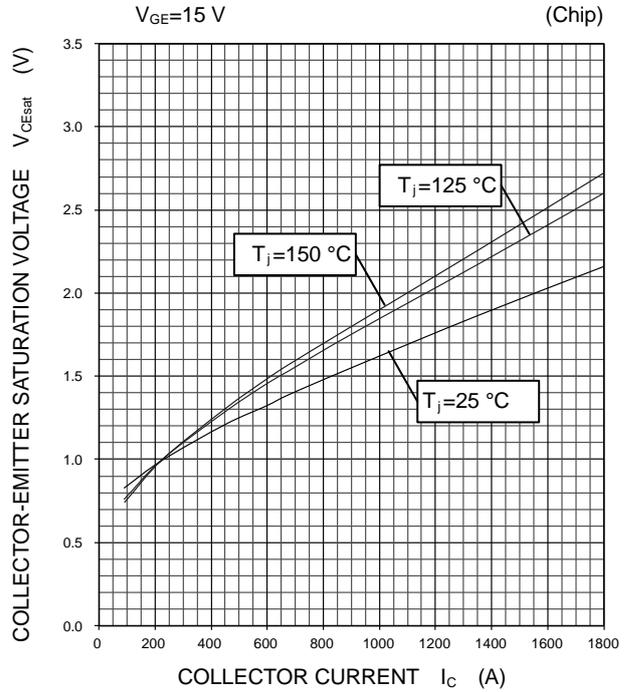
OUTPUT CHARACTERISTICS

(TYPICAL)



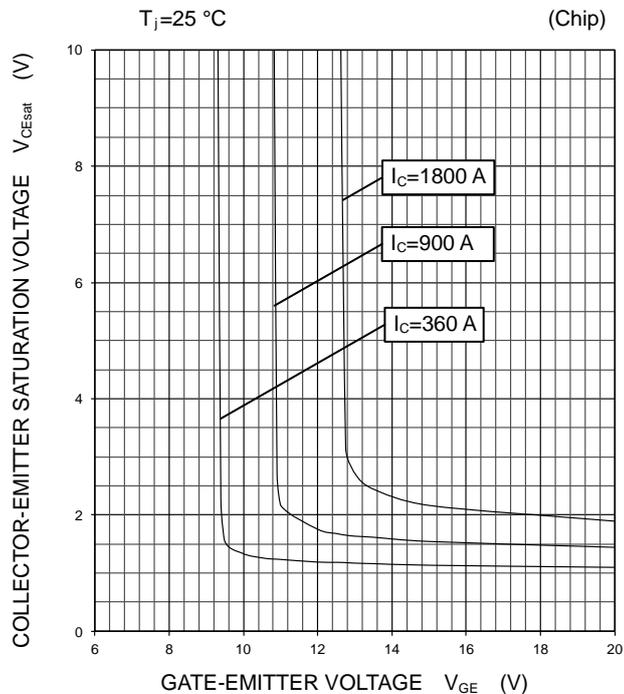
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS

(TYPICAL)



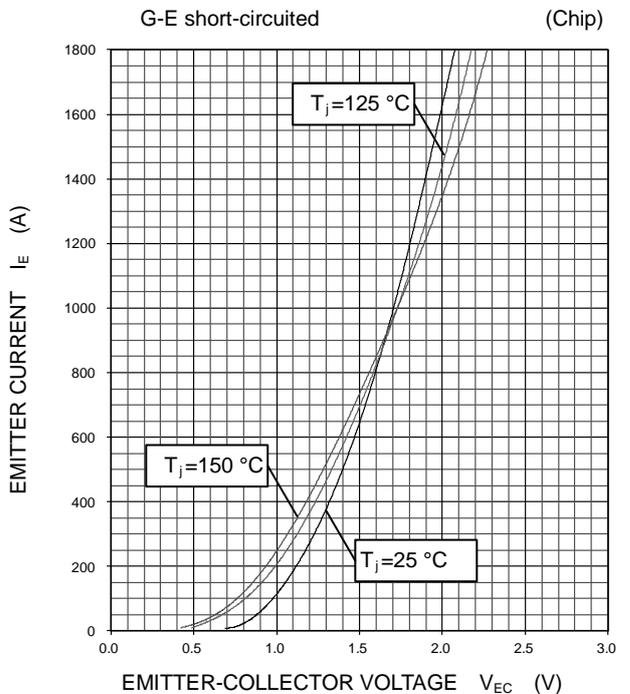
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS

(TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS

(TYPICAL)



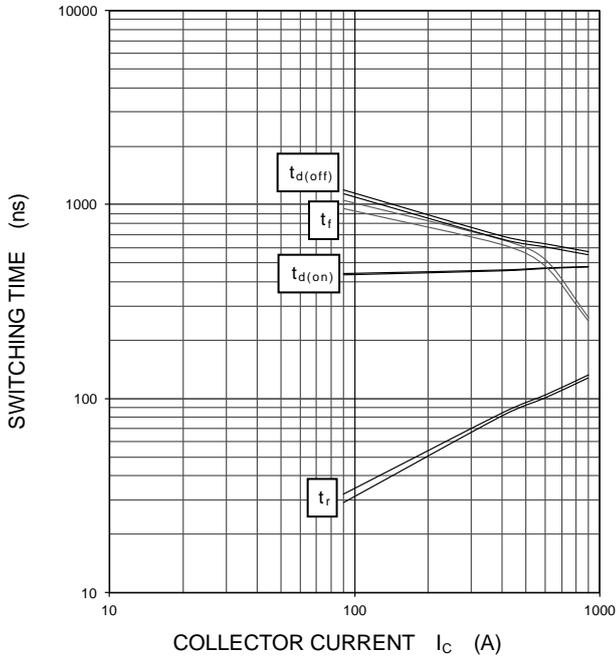
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HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

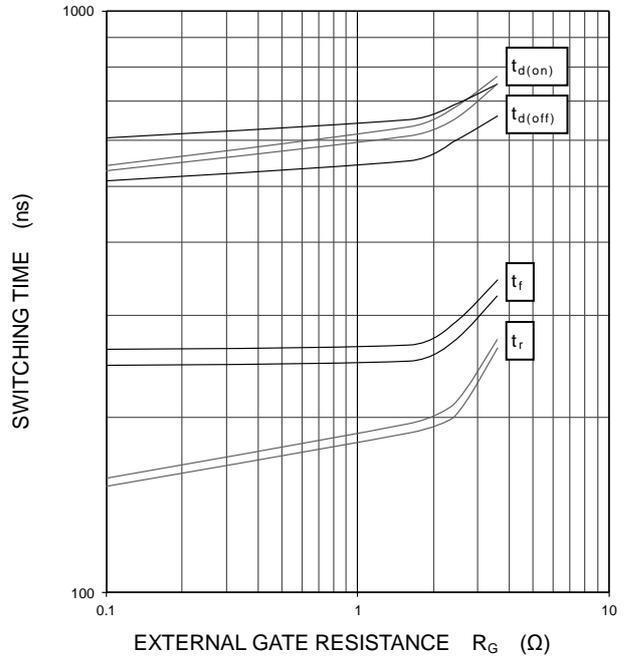
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



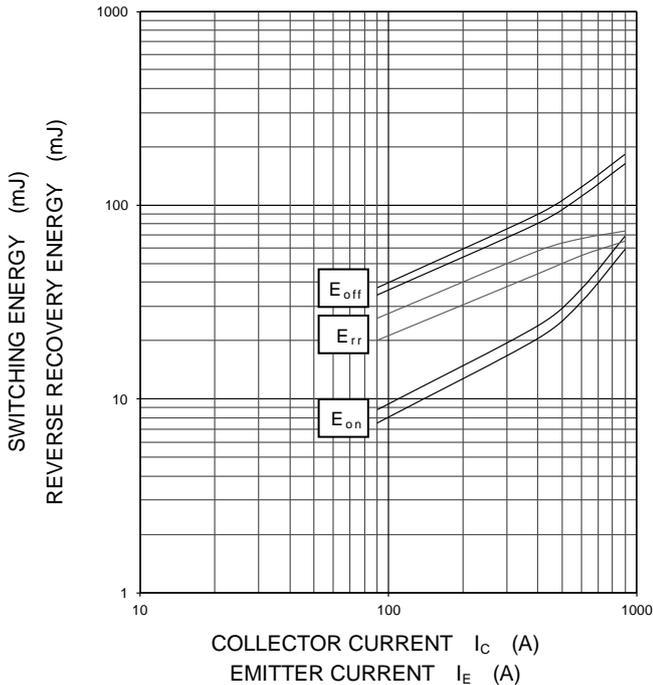
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $I_C=900\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



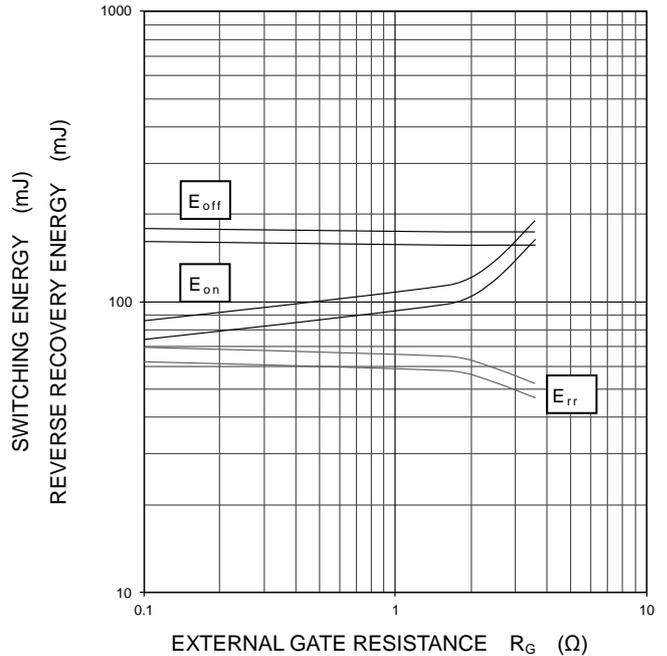
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
INDUCTIVE LOAD, PER PULSE
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $I_C/I_E=900\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
INDUCTIVE LOAD, PER PULSE
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



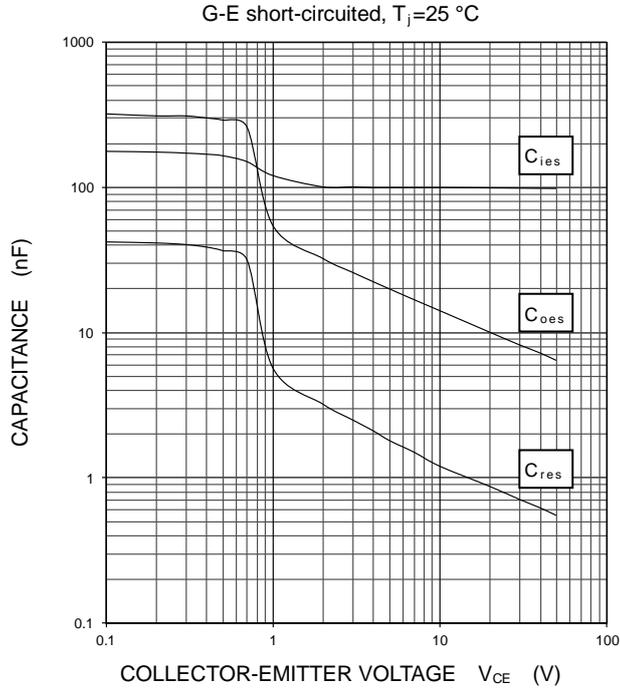
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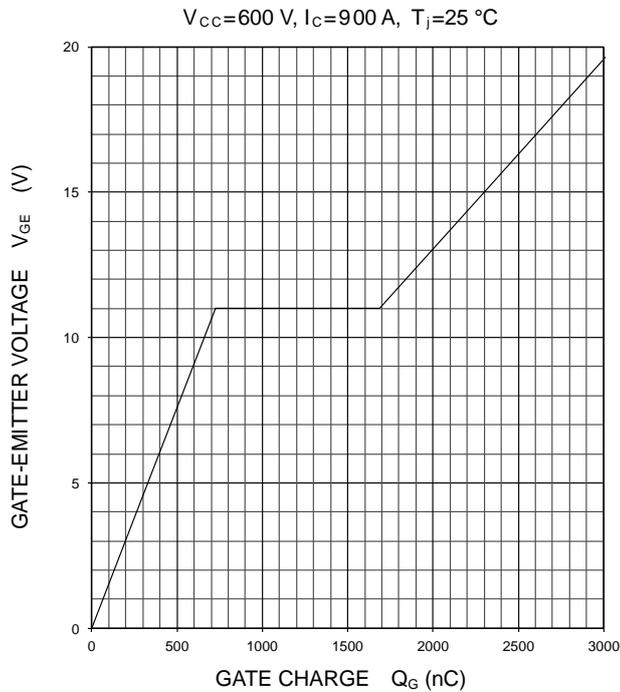
PERFORMANCE CURVES

CAPACITANCE CHARACTERISTICS

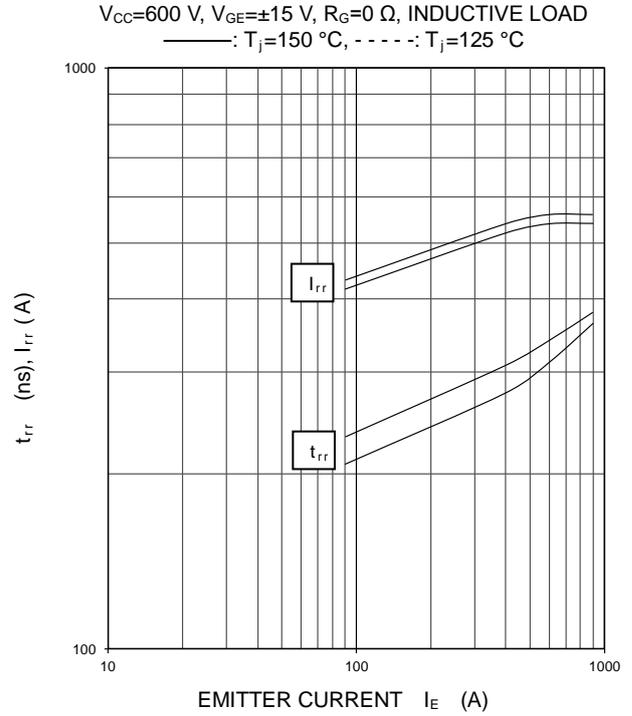
(TYPICAL)



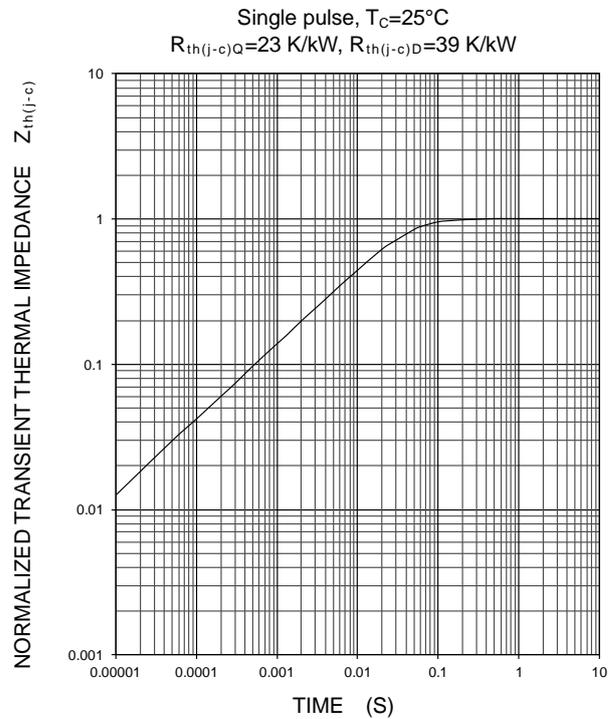
GATE CHARGE CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)



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